

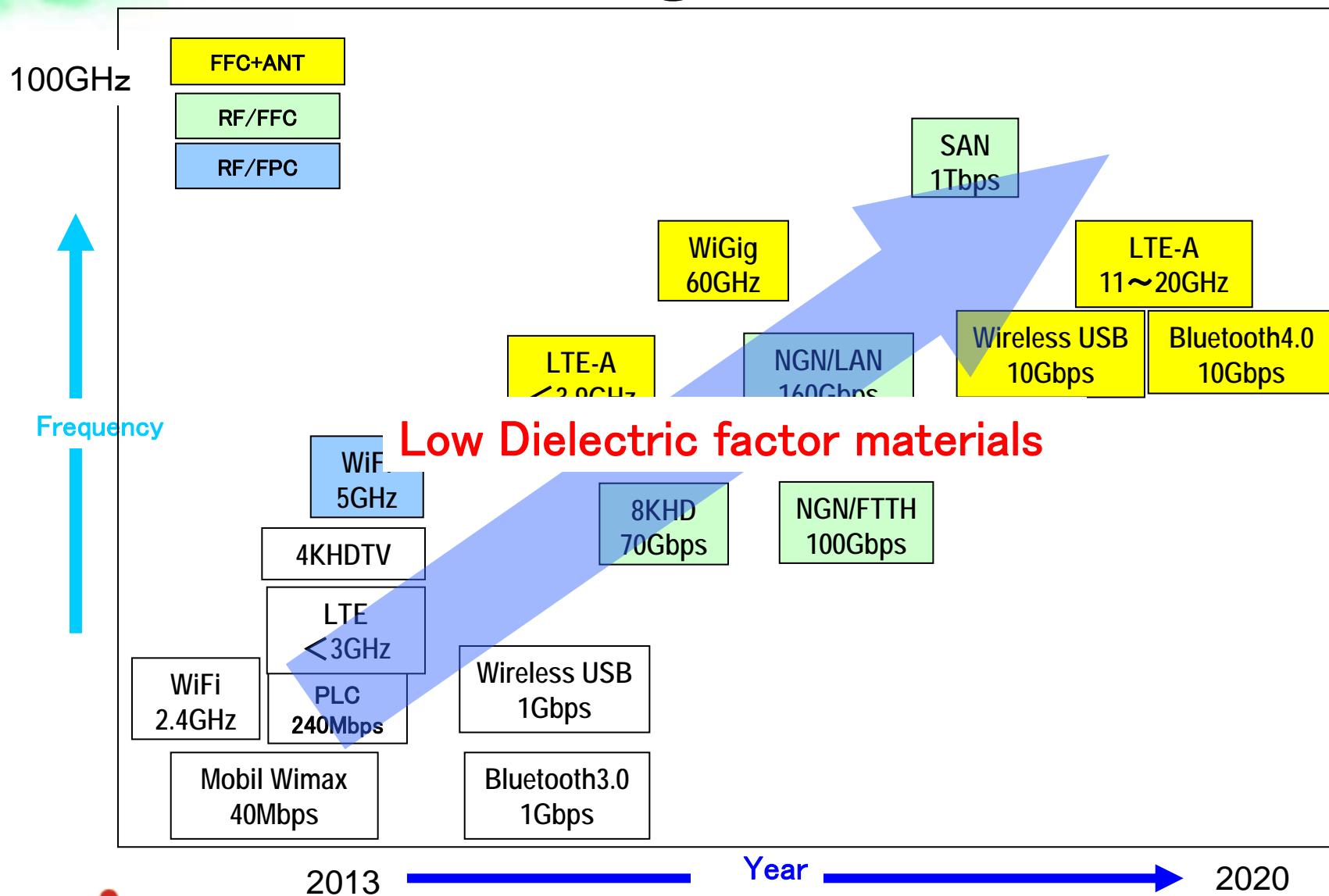
New Functional Insulating Film for High-speed Transmission Circuit

Shin Teraki
NAMICS CORPORATION
ADFLEMA Division

Outline

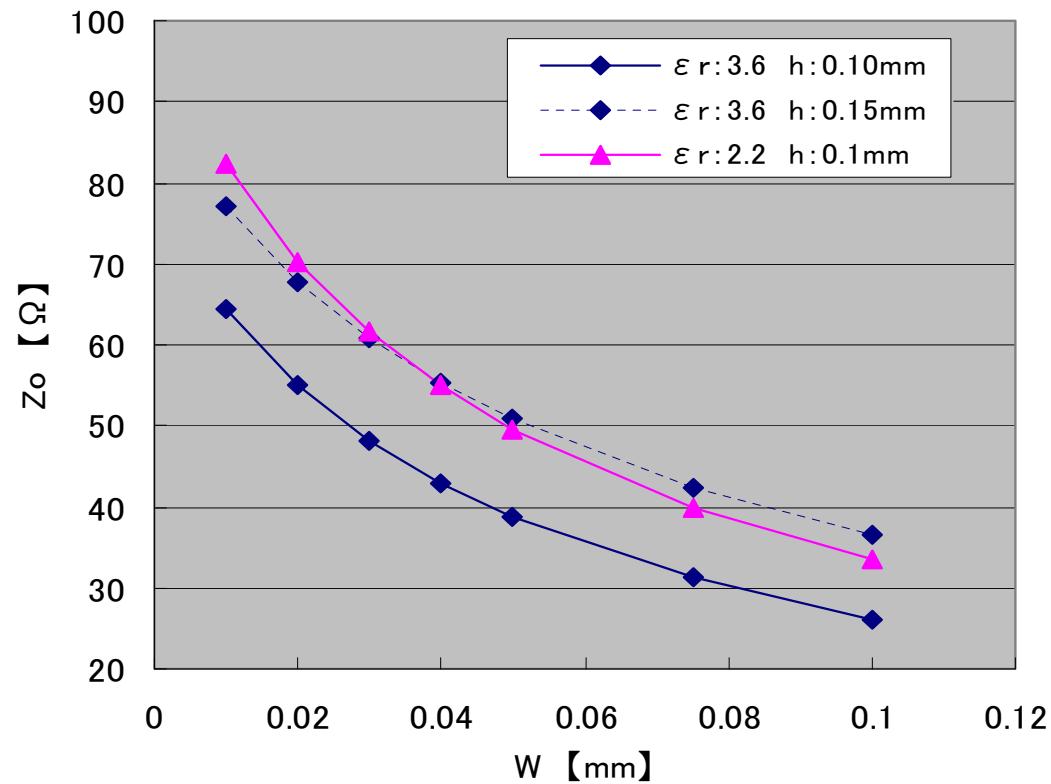
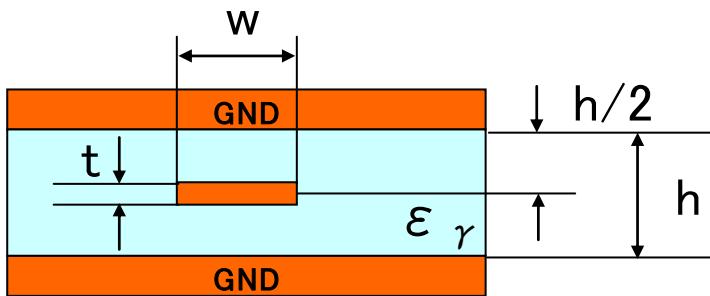
- ◆ Background
- ◆ Approach to an organic insulation material for high frequency
- ◆ Film Properties
- ◆ Application to high frequency circuit
- ◆ Summary

Background

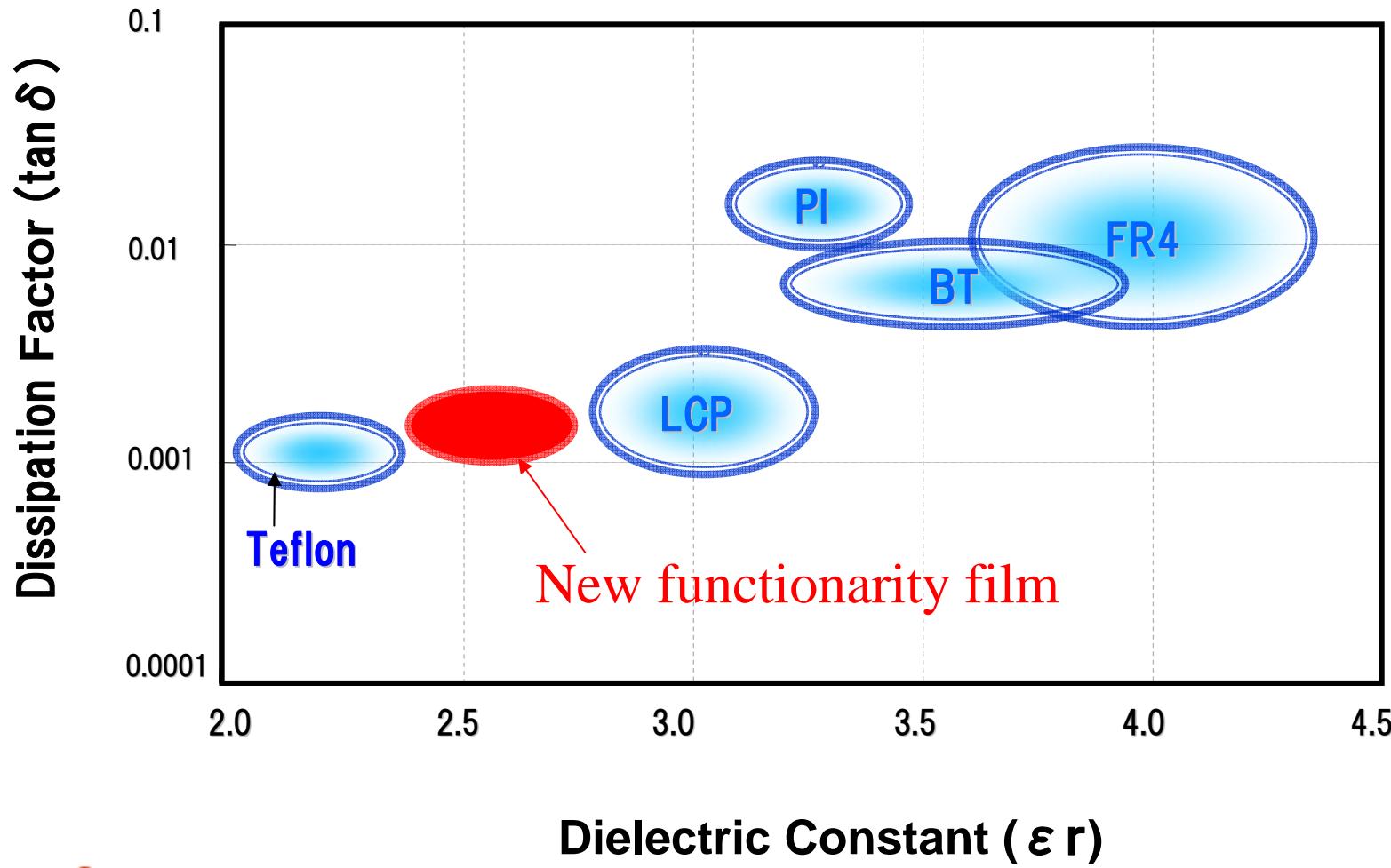


The merit of a low dielectric constant material

$$Z_0 = \frac{60}{\sqrt{\epsilon_r}} \ln \left(\frac{4h}{0.67 \pi (0.8w+t)} \right)$$



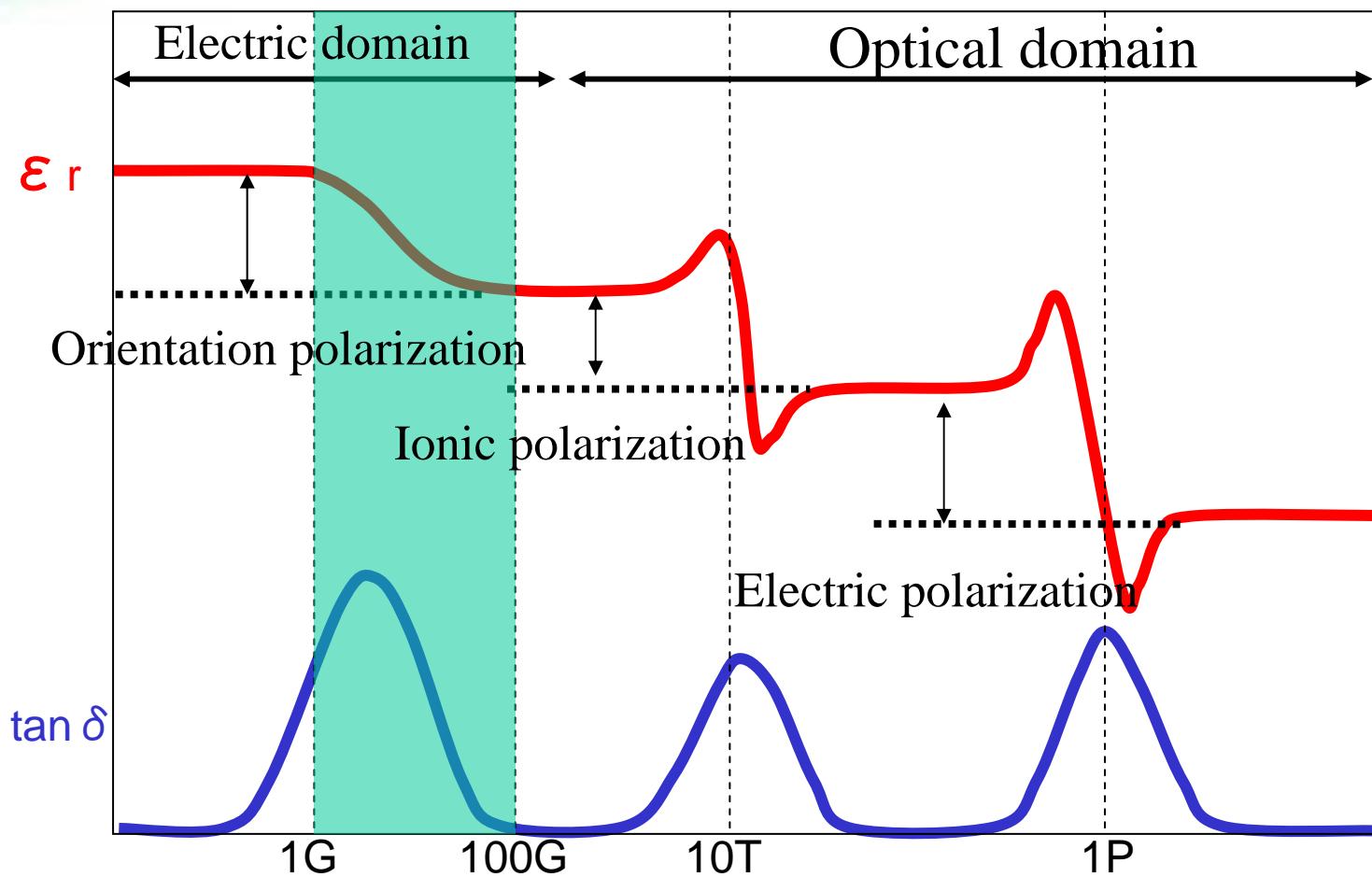
Dielectric property of various materials



Outline

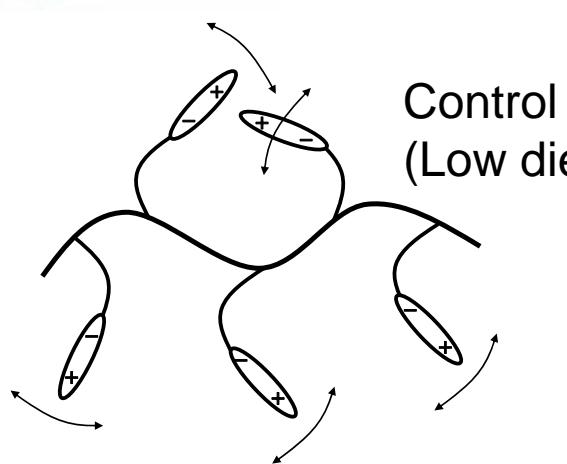
- ◆ Background
- ◆ Approach to an organic insulation material for high frequency
- ◆ Film Properties
- ◆ Application to high frequency circuit
- ◆ Summary

Approach to an organic system

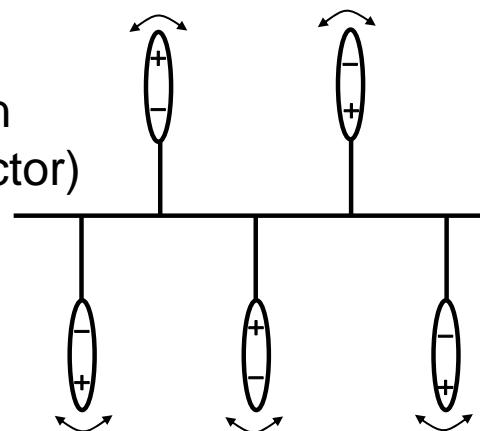


In a high frequency band in a GHz range,
an influence of orientational polarization needs to be minimized.

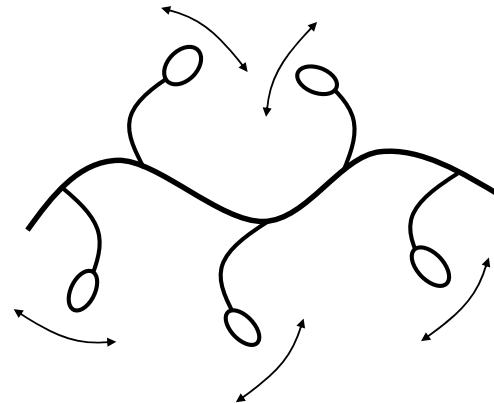
Approach to an organic system



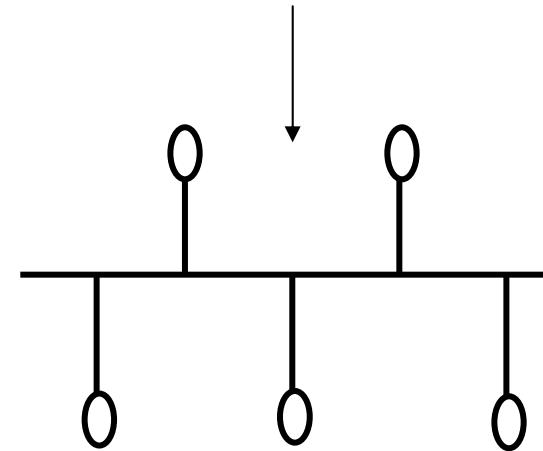
Control of a molecular motion
(Low dielectric dissipation factor)



Rigid main structure



↓
Low polarity
(Low Dielectric constant)



↓
Low Dielectric constant
Low dielectric dissipation factor

Approach to an organic system

Clausius-Mosotti

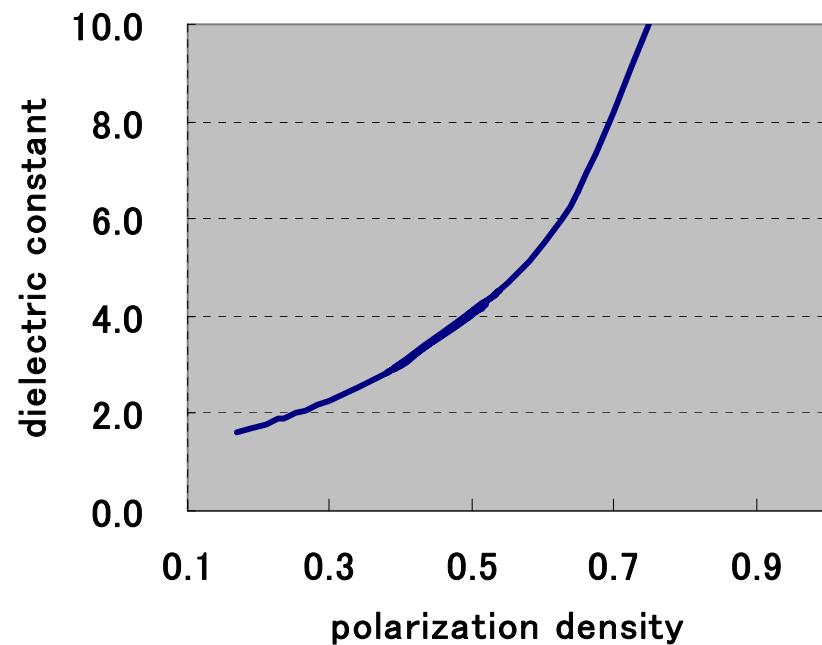
$$\epsilon_r = (1 + 2a) / (1 - a)$$

a : Polarization density $\sum P_m / \sum V_m$

Pm : Molar Polarization, Vm : Molar volume,

Atom group	Pm	Vm	a	ϵ_r
—CH2—	4.7	23.9	0.24	1.95
—CH<	3.6	9.5	0.38	2.84
>CH<	2.6	4.8	0.54	4.52
—  —	25	65.5	0.38	2.84
—O—	5.2	10	0.52	4.25
—COO—	15	23	0.65	6.57
—CO—	10	13.4	0.75	10.00
—F	1.8	10.9	0.17	1.61
—CH3	5.6	23.9	0.24	1.95
—Br	11.7	30	0.39	2.92
—Cl	9.5	19.9	0.477	3.74
—CN	11	19.5	0.56	4.88
—OH	6	9.7	0.62	5.87

Relation between ϵ_r ,
and polarization density



Outline

- ◆ Background
- ◆ Approach to an organic insulation material for high frequency
- ◆ Film Properties
- ◆ Application to high frequency circuit
- ◆ Summary

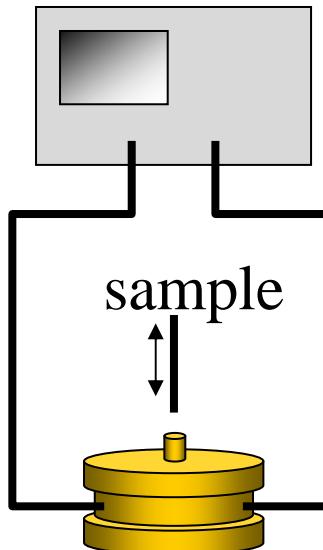
Properties of thermosetting film

Item	Unit	Low Dk, Df	Method
Dielectric constant	2 GHz	2.4	Cavity Resonator
Dissipation factor	2GHz	0.0025	
Copper peel strength	N/cm	10	JIS C6471
Tensil strength	MPa	42	ASTM D 882
Elongation	%	250	ASTM D 882
Tensil modulus	MPa	800	ASTM D 882
Glass transition temp.	°C	190	DMA
CTE(α1)	ppm/°C	110	TMA
Volume resistance	E15Ω cm	1	JIS C2170
Thermal Decomposition temp.	°C	370	TG-DTA
Water absorption	%	<0.1	25°C, 24hr

High frequency properties of the film

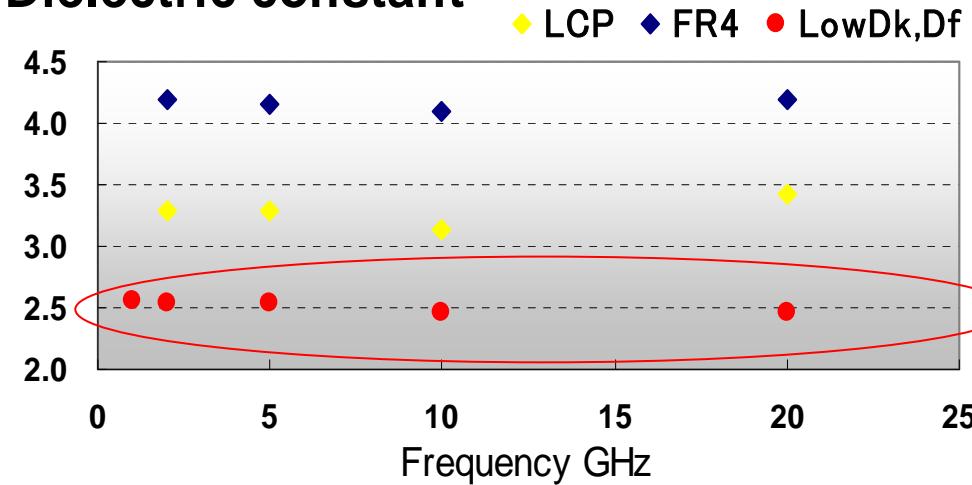
Frequency dependence

Method
Cavity Resonator
Frequency
1G–20GHz

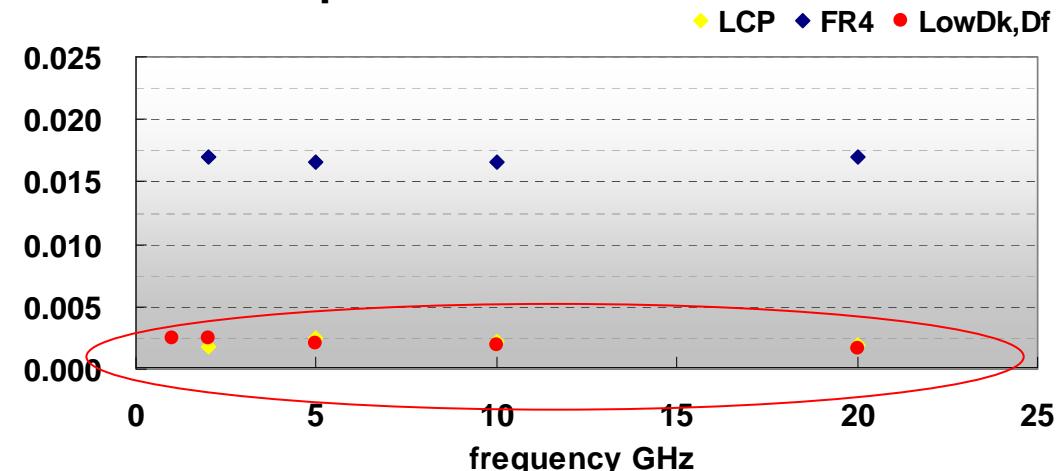


Cavity Resonator

Dielectric constant



Dielectric dissipation factor



High frequency properties of the film

Temperature dependence

Method

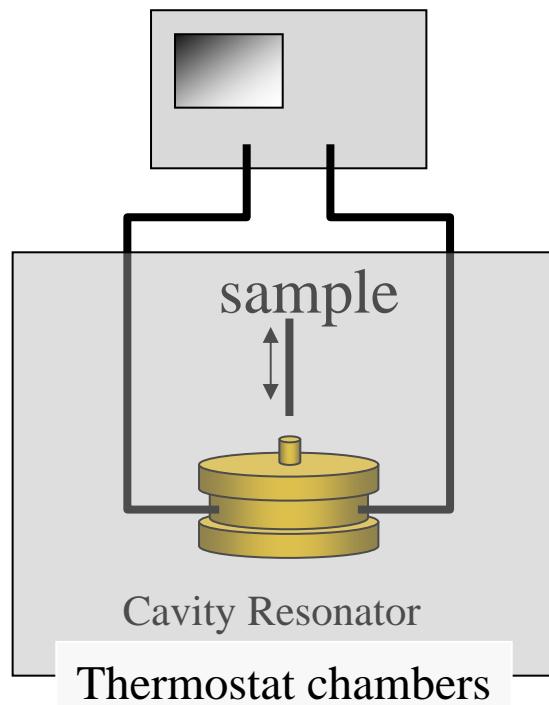
Cavity Resonator

Frequency

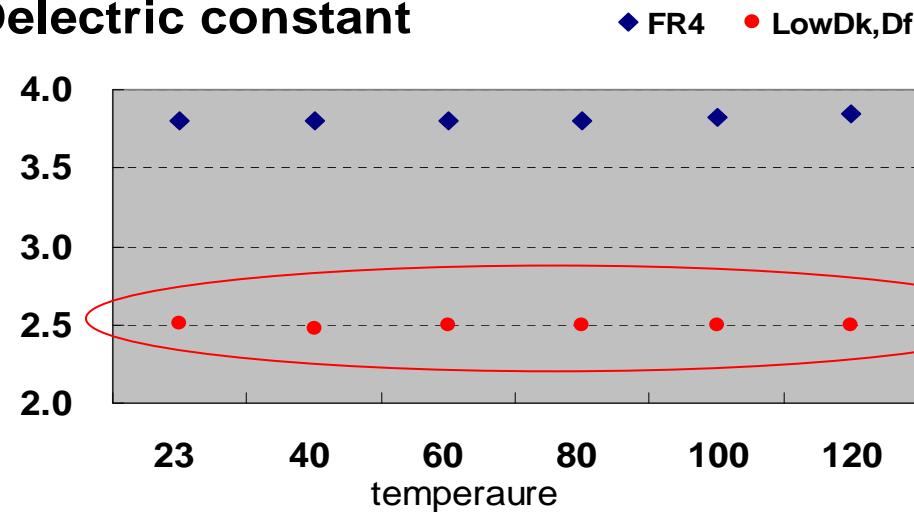
10GHz

Condition

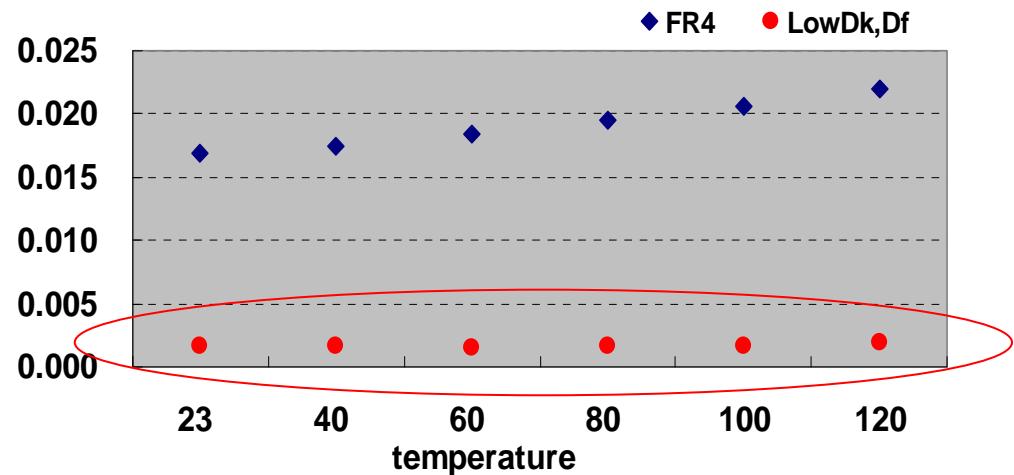
temp.23, 40, 60, 80, 100, 120°C



Dielectric constant



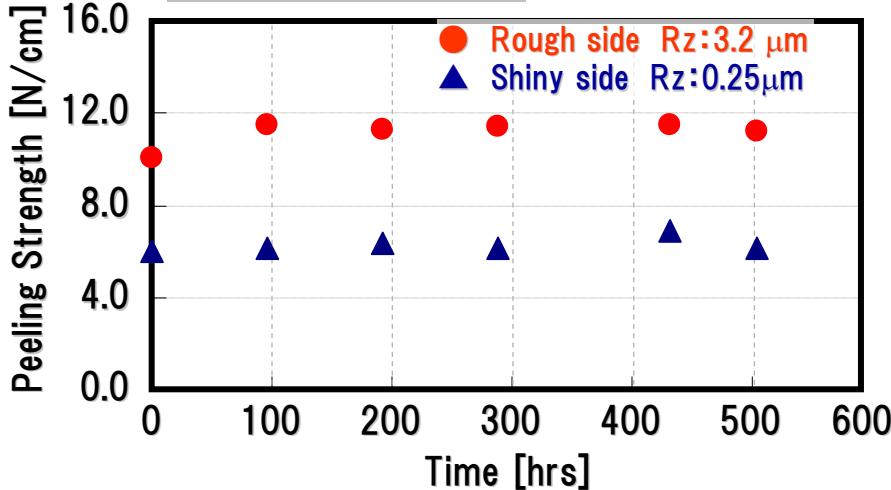
Dielectric dissipation factor



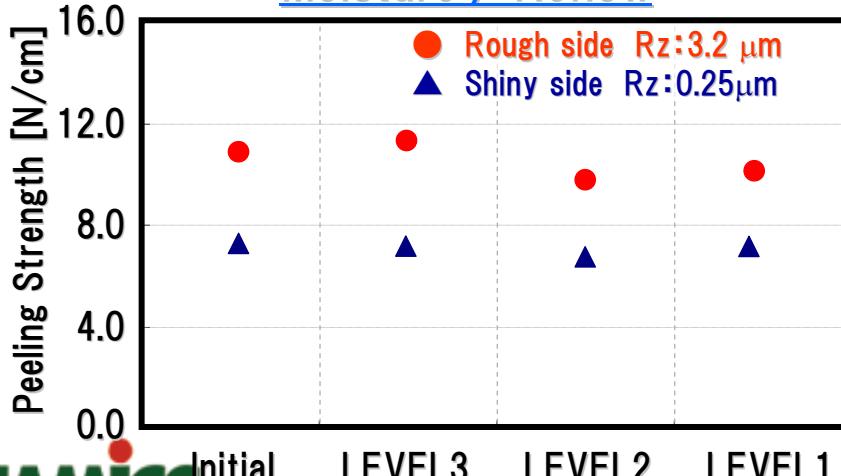
Properties

Adhesive Reliability

Leaving at 125°C



Moisture / Reflow



【Cu Peeling Strength】

OCu Foil

Electrolytic 3EC-VLP 12μm

OLamination Condition

200°C × 60min, 1MPa, Vacuum <10KPa

O180° Peeling Test(@RT)

Peeling Speed 50mm/min

JEDEC LEVEL1-2-3

Level1:168hrs 85°C/85%RH & 260°C × 3times

Level2:168hrs 85°C/60%RH & 260°C × 3times

Level3:192hrs 30°C/60%RH & 260°C × 3times

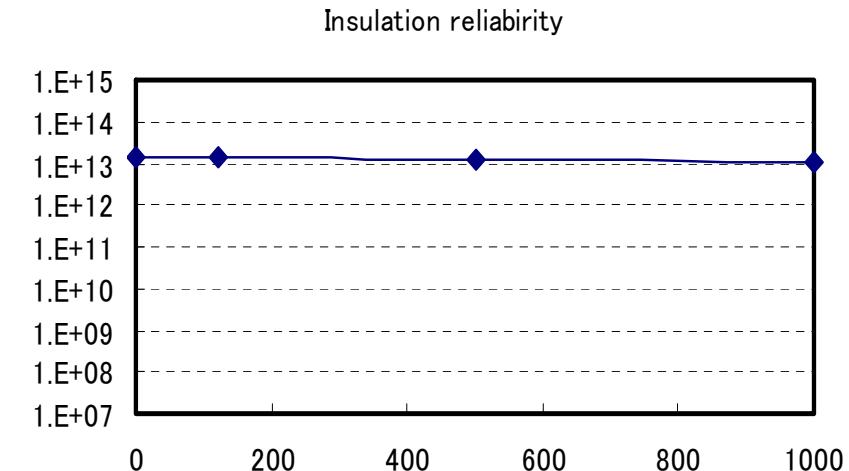
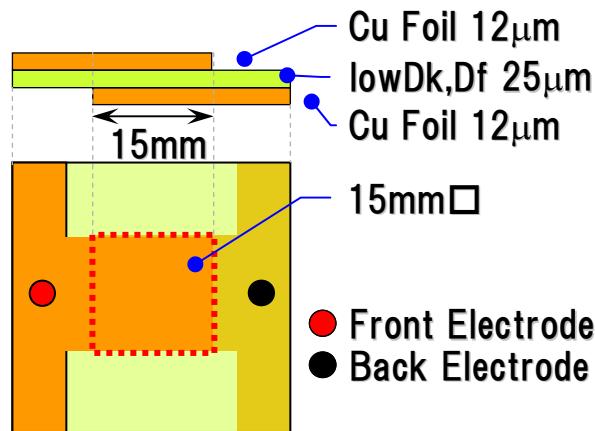
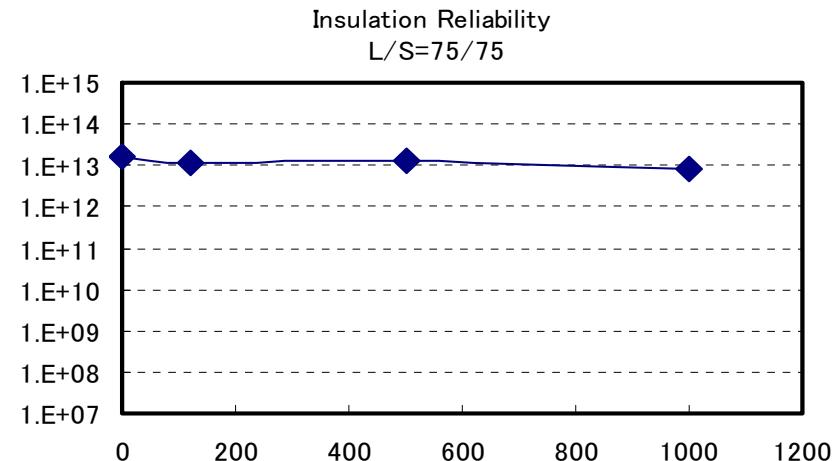
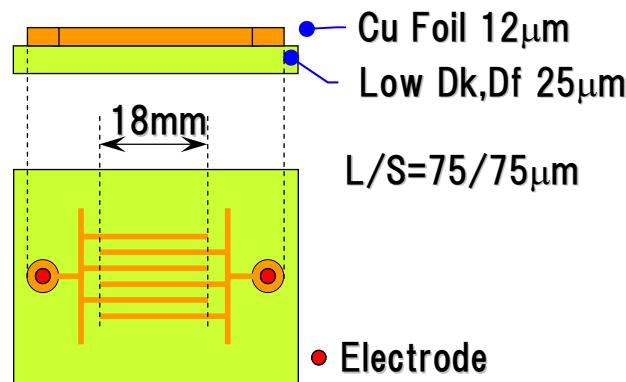
Insulation Reliability

15

Condition

Pretreatment : JEDEC Level 3 30°C 60% 192hr → Reflow peek temp. 260°C × 3

Test condition 85°C/85%RH/DC30V, 1000h



Outline

- ◆ Background
- ◆ Approach to an organic insulation material for high frequency
- ◆ Film Properties
- ◆ Application to high frequency circuit
- ◆ Summary

Application

FPC for high-speed transmission circuit
High-speed & High reliability Multilayer Board

- Ex. ◆ High speed transmission cable
◆ Antenna substrate
◆ PWB with embedded devices

FPC ⇒ Bonding-sheet、Cover-lay

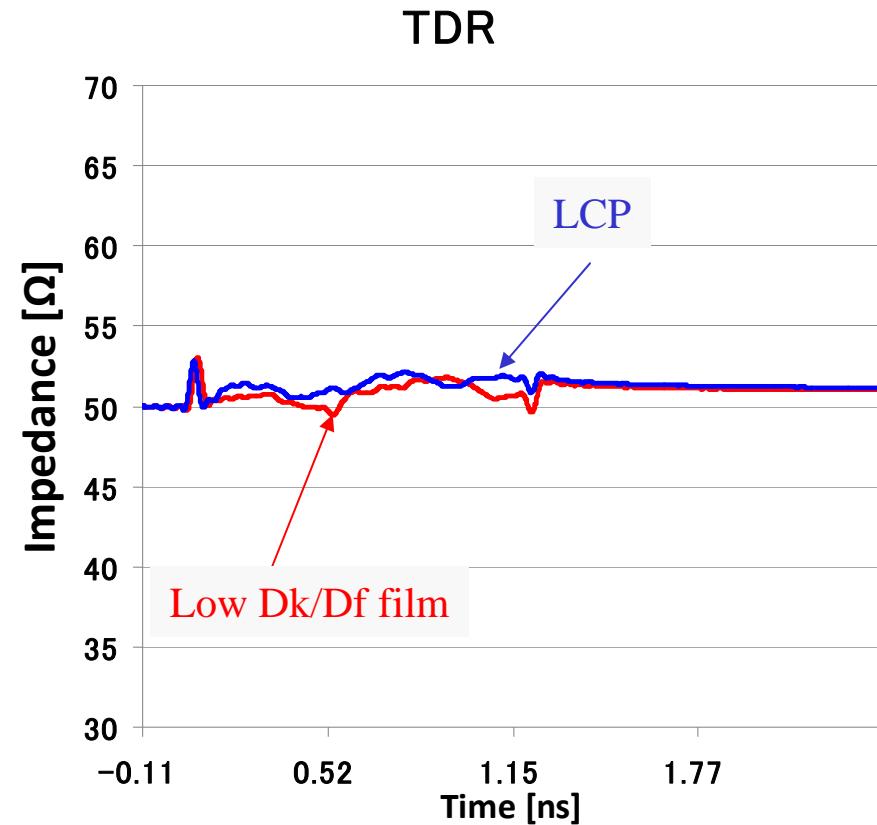
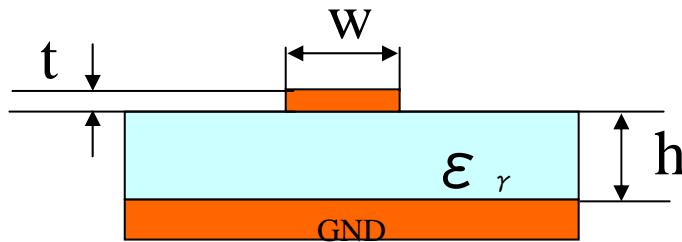
Multilayer Board ⇒ Build-Up layer

Characteristic Impedance

18

Microstrip line

$$Z_0 = \frac{87}{\sqrt{\epsilon_r + 1.41}} \ln \left(\frac{5.98h}{(0.8w+t)} \right)$$



	ϵ_r	Thickness [μm]	Line width [μm]	Impedance [Ω]
LCP	3.0	50	112	50
Low Dk.Df	2.4	50	130	50

Return Loss (S11)

19

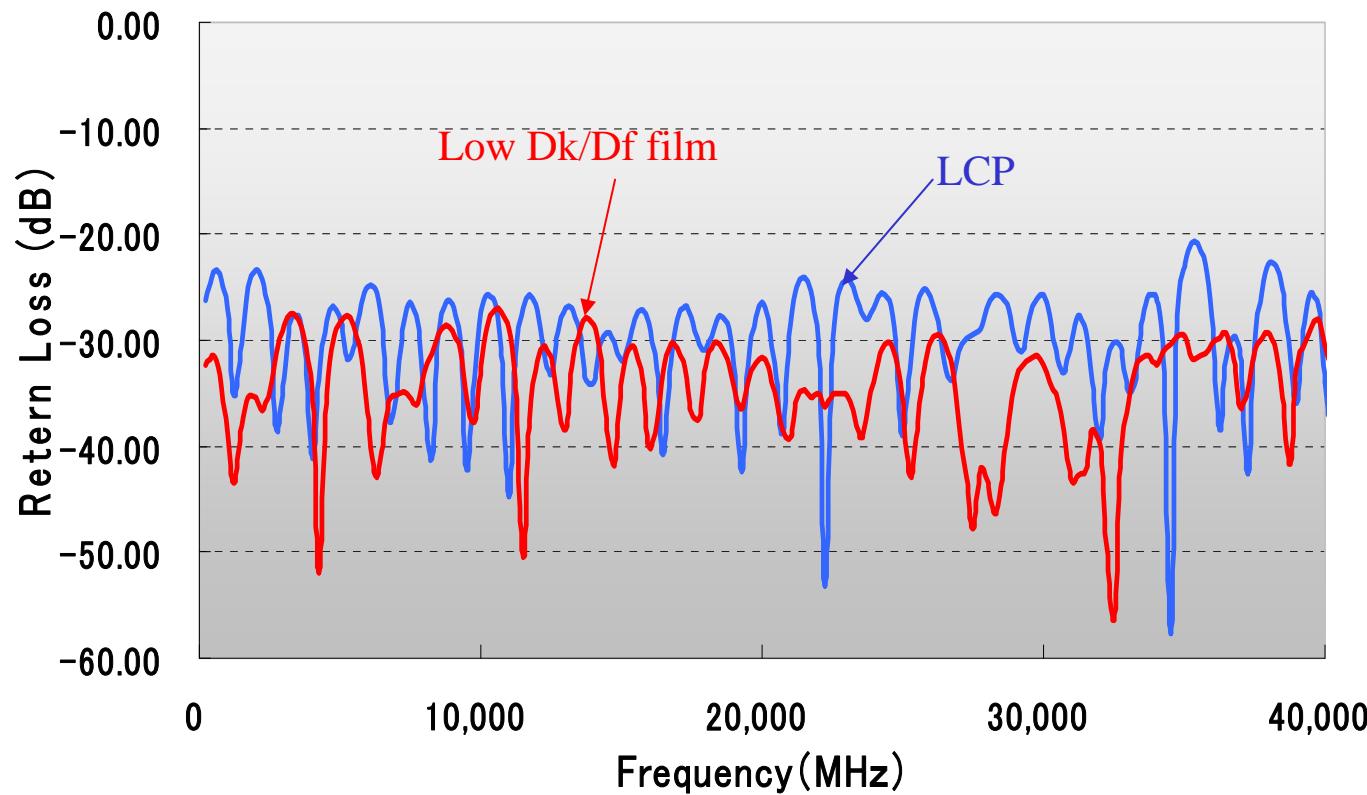
Machine : E8363B (Agilent Technologies)

Frequency : 10M–40GHz

Insulating Layer : 50 μ m

Wiring Length : 70mm

Wiring Thickness : 18 μ m



Insertion Loss (S21)

20

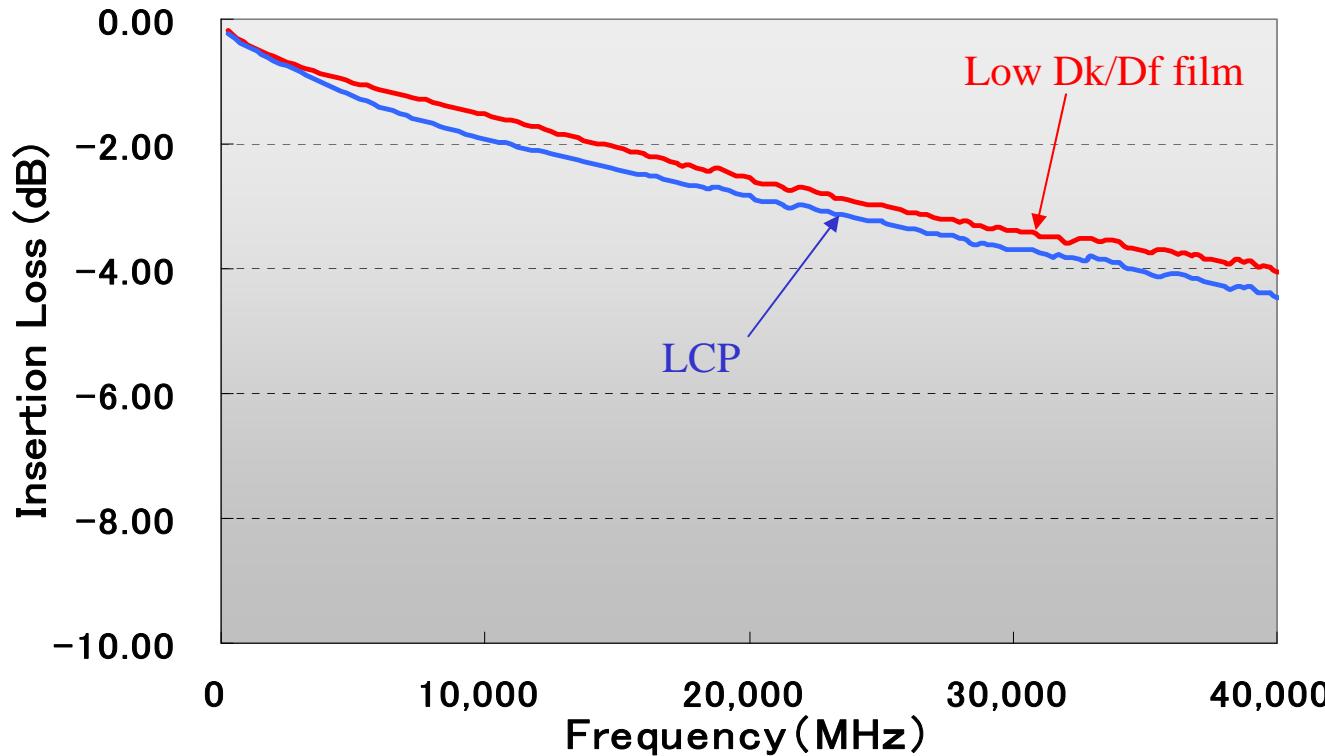
Machine : E8363B (Agilent Technologies)

Frequency : 10M–40GHz

Insulating Layer : 50 μ m

Wiring Length : 70mm

Wiring Thickness : 18 μ m



Summary

Our new functional film is excellent in high frequency characteristics, heat resistance, and moisture resistance.

It is a promising film to apply to various electronic devices which require high-speed large-volume data processing.

For future study, we will put more effort into reducing a further dielectric constant and a low dielectric dissipation factor.